

The schematic diagram illustrates the RF front end and baseband processor for the 4G LTE module. It features two SA612 ICs (U1 and U2) and two TS464 comparators (IC1A and IC1B). The circuit is powered by +6V0 and GND. Key components include:

- RF Front End:** Includes an RF input (X1), a BU-SMA-V connector, and a 49R9 resistor (R3). The RF signal is processed by U1 and U2, which have various pins for VCC, OSC, and OUT.
- Baseband Processor:** U1 and U2 are configured with various resistors (R1, R2, R3, R4, R5, R6, R7, R8, R9, R10, R11, R12, R13, R14, R15, R16, R17, R18, R19, R20, R21, R22, R23, R24, R25, R26, R27, R28, R29, R30) and capacitors (C1, C2, C3, C4, C5, C6, C7, C8, C9, C10, C11, C12, C13, C14, C15, C16, C17, C18, C19, C20, C21, C22, C23, C24) to filter and amplify the signals.
- Comparators:** IC1A and IC1B are TS464 comparators used for signal processing. They are configured with various resistors (R1, R2, R3, R4, R5, R6, R7, R8, R9, R10, R11, R12, R13, R14, R15, R16, R17, R18, R19, R20, R21, R22, R23, R24, R25, R26, R27, R28, R29, R30) and capacitors (C1, C2, C3, C4, C5, C6, C7, C8, C9, C10, C11, C12, C13, C14, C15, C16, C17, C18, C19, C20, C21, C22, C23, C24) to filter and amplify the signals.
- Power and Grounding:** The circuit is powered by +6V0 and GND. Various capacitors (C1, C2, C3, C4, C5, C6, C7, C8, C9, C10, C11, C12, C13, C14, C15, C16, C17, C18, C19, C20, C21, C22, C23, C24) are used for decoupling and filtering.

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